

FILE EDIT VIEW WINDOW

FILE EDIT VIEW WINDOW

SEARCH

SEARCH

S5: (505929) growth

S6: (80308) epitaxial

S7: (508323) selective

S8: (3751) nonselective

S9: (10682) non adj selective

S10: (13714) nonselective (non adj selective)

S11: (32926) epitaxial adj growth

S12: (47) ((nonselective (non adj selective)) adj (epitaxial adj growth))

S13: (29) ((nonselective (non adj selective)) adj (epitaxial adj growth))

S14: (110307) single adj crystal\$3 monocrystal\$3 mono adj crystal\$3

S15: (186733) (polysilicon poly adj silicon polycrystal\$4 poly adj crysta

S16: (320407) collector

S17: (17007) (single adj crystal\$3 monocrystal\$3 mono adj crystal\$3u)

S18: (227) ((single adj crystal\$3 monocrystal\$3 mono adj crystal\$3u) w

S19: (189) (((single adj crystal\$3 monocrystal\$3 mono adj crystal\$3u) i

S20: (17) (((single adj crystal\$3 monocrystal\$3 mono adj crystal\$3u) v

S21: (2111568) thick\$4

S22: (18) (((single adj crystal\$3 monocrystal\$3 mono adj crystal\$3u) w

S23: (3) "05062991"

S24: (2) "5323032" pn.

Favorites

Tagged (4)

UDC

Queue

SEARCH

SEARCH

(((single adj crystal\$3 monocrystal\$3 mono adj crystal\$3
) with ((polysilicon poly adj silicon polycrystal\$4 poly adj crystal\$4)
) with collector) with thick\$4

Jan. 2005

U	Inventor	Document	Issue	P	Title	Current	Current X	Retrieval	S	C	P	Image	Doc	P
1	Sato, Hidek	US 200400	2004	2	Semiconductor device and method for	257/19							US 20040	
2	Chen, Huaji	US 200401	2004	8	Self-aligned mask formed utilizing diffe	438/16							US 20040	
3	Washio, Ka	US 200302	2003	4	Semiconductor device	257/19	257/E21.3						US 20030	
4	YAMAZAKI, US	200100	2001	2	A METHOD OF PRODUCING A SEMIC	438/49	257/E21.3						US 20010	
5	Heinemann, US	674056	2004	1	Bipolar transistor and method for prod	438/30	257/197						US 67405	
6	Sato, Fumi	US 668052	2004	3	Semiconductor device with reduced el	257/58	257/587						US 66805	
7	Washio, Ka	US 660017	2003	3	Heterojunction bipolar transistor	257/19	257/191						US 66001	
8	Ehwald, Ka	US 646531	2002	6	Bipolar transistor and method for prod	438/34	257/E21.1						US 64653	
9	Marty, Mic	US 646531	2002	7	Process for producing a bipolar transi	438/32	257/E21.3						US 64653	
10	Laurens, M	US 617189	2001	1	Method of manufacturing BICMOS inte	438/20	257/E21.6						US 61718	